

Proposed Pinout for FE-I Chips

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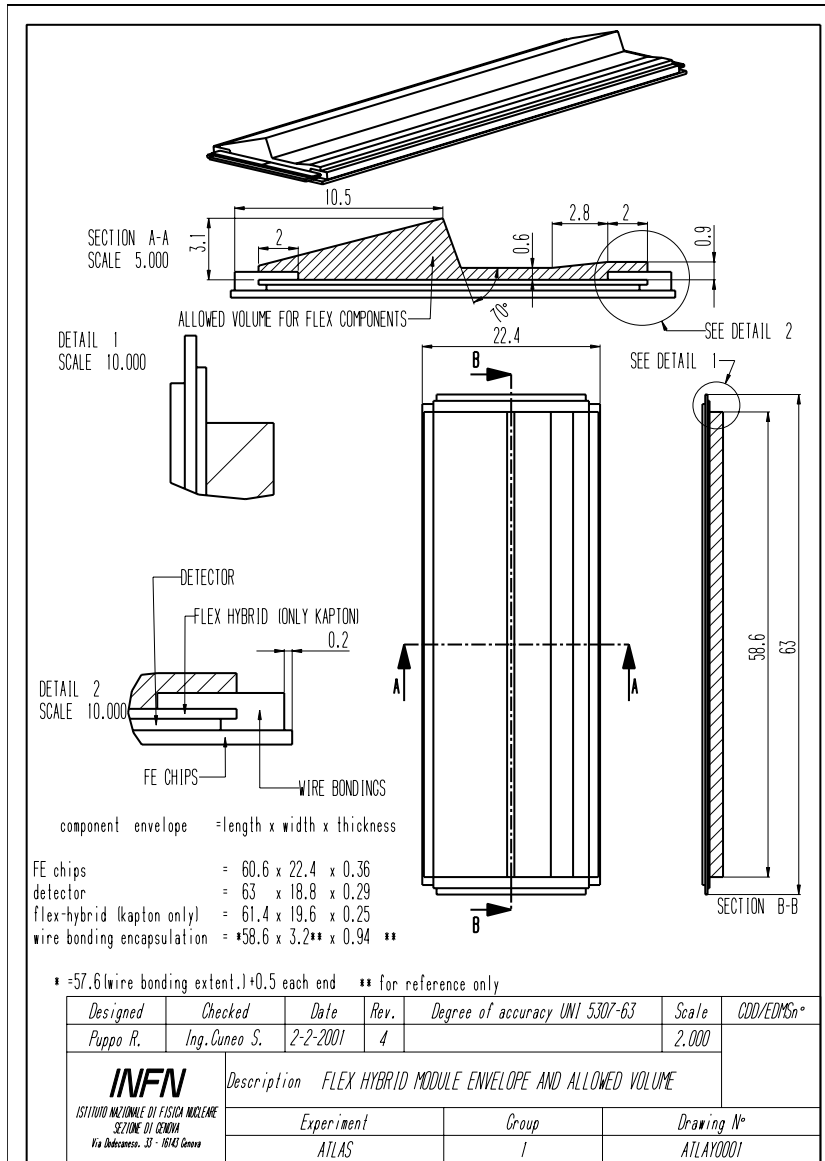
Geometry and Pinout issues:

- Need to match production pinout and geometry to proposed module envelope.

Propose final pinout, satisfying these constraints

Overview of Module Envelope

Summarize constraints on module envelope:



Constraints on FE die size:

- Present prototypes use:
7.2x(8.0+2.8)mm design size
with 0.1mm dicing zone all around:
7.4x11.0mm as-cut die size.
- Production size agreed to be same:
Provides total chip envelope in z of
 $8 \times 7.4 + 7 \times 0.2 = 60.6\text{mm}$

Constraints on FE bonding region:

- End chips have a constraint on the region which may be wire-bonded, in order to provide good Z overlap. Bonds must fit in central 57.6mm of module, meaning central 4.4mm out of the 7.4mm as-cut die width.
- If we retain the present 150μ bond-pad spacing, that corresponds to 30 bonding pads (4.35mm + pad size).

Proposed Final FE Chip Pinout (30 bonded pads):

- Total of 10 power pins, positioned at 1/4 and 3/4 points in die (mirrored) :
 - p11, p38 VDDA
 - p12, p37 AGnd
 - p13, p36 Shield
 - p14, p35 DGnd
 - p15, p34 DVdd
- Total of 1 analog pin (intended largely for lab calibration at this time):
 - p20 VCal
- Total of 9 Command and Address pins (GA closer to DGnd):
 - p16 - p19 GA0 - GA3
 - p21 CCK
 - p22 DI
 - p23 LD
 - p32, p33 STRn, STRp
- Total of 6 control pins (all LVDS pins are grouped together):
 - p26, p27 SYNCn, SYNCp
 - p28, p29 XCKn, XCKp
 - p30, p31 LV1n, LV1p
- Total of 2 output pins (now located in chip center for easier Flex routing)
 - p24, p25 DOn, DOp
- Total of 2 detector pins:
 - p10 DGuard
 - p39 DGrid

To reach this, have removed 18 pads from present pinout:

- RSTb, and Analog pins (I1-I8, and VCCD/VTH)
- All monitoring pins (MonHit, MonSel, MonRef, MonAmp)
- Propose to retain most on the die, in locations compatible with present floorplans:
- Total of 1 control pin:

p40 RSTb

- Total of 11 current monitor pins (may not all be used):

p1 I1

p2 I2

p3 I3

p4 I4

p5 I5

p6 I6

p7 I7

p8 I8

p9 I9

p41 I10

p42 I11

- Total of 6 special monitoring pins:

p43, p44 MonHitn, MonHitp

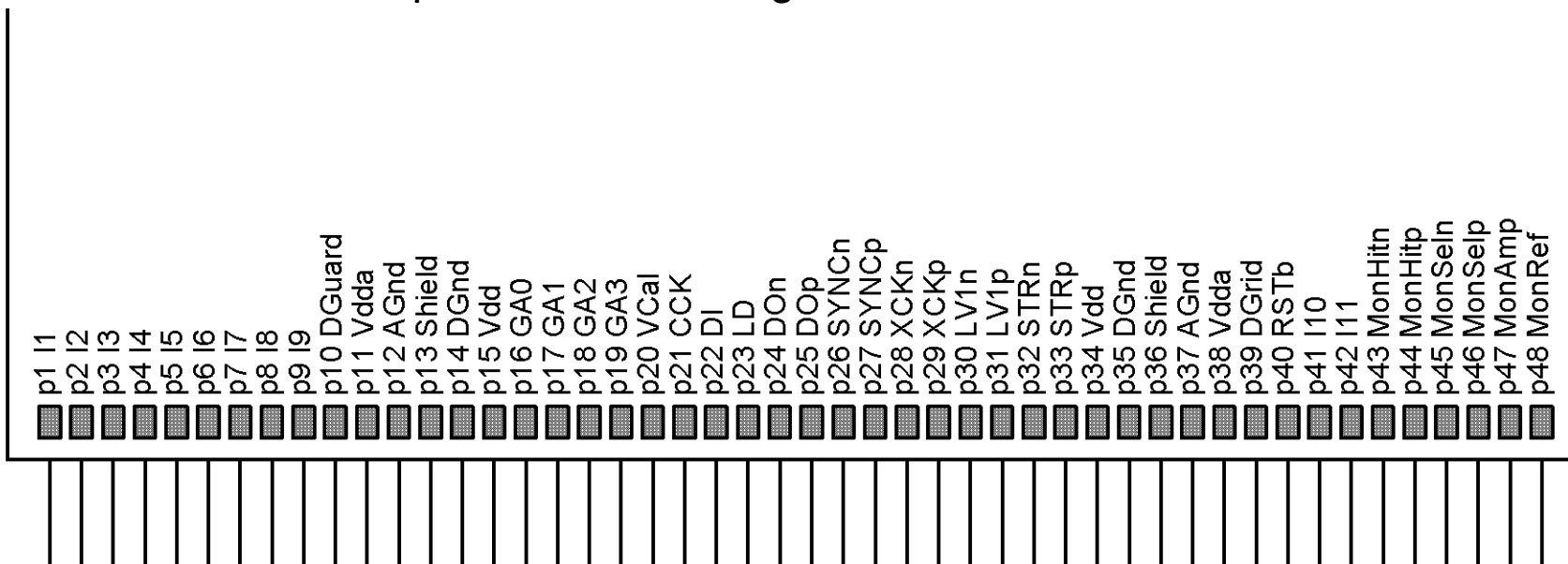
p45, p46 MonSeln, MonSelp

p47 MonAmp

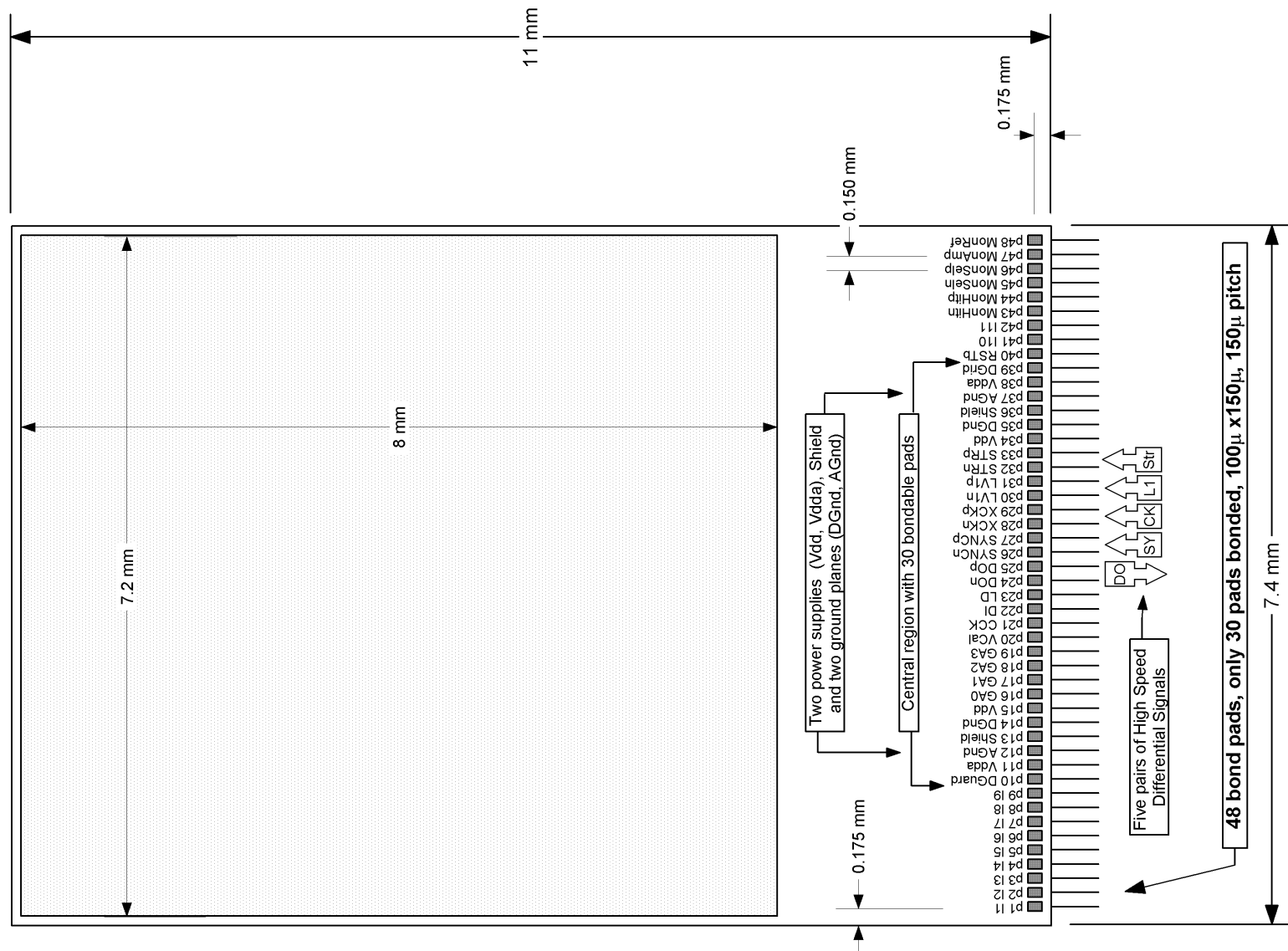
p48 MonRef

Proposed Pad Geometry:

- Increase present pad size to $100\mu \times 150\mu$ rectangle, with 150μ pitch, to provide more pad area for rebonding. Include MCM-D bump-bondable I/O pads with the same geometry used in FE-D (relative to the bottom of the wire bond pads).
- Continue to locate pads close to the lower die edge, as for demonstrator chips.
- The present demonstrator geometry has 48 pads, with centers along a line 175μ above the bottom (referenced to the as-cut die size of $7.4 \times 11.0\text{mm}$). The first pad center is also 175μ from the vertical edge referenced to the as-cut die size.
- Propose that this pad placement would be retained, and only the central 30 pads would be used for production bonding:



Overall Chip Geometry:



Status of this Proposal:

- This proposal has been discussed with FE design community, and has been presented and discussed during the Feb Pixel week in the Flex and Module meetings.
- Minor modifications to the original proposal were made, and this should now be the final draft of the proposal.
- Further modifications in the non-bonded pads could still be considered.
- It will be circulated one more time, and then considered approved for the FE-I design and the Flex 3 designs.
- Probe card design based on this pinout should also begin soon in order to prepare for the arrival of the new chips.